



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

7/A
4/25/03
Mullish

In re Patent Application of)
Hideto Ohnuma)
Serial No. 10/053,542)
Filed: January 24, 2002)
For: METHOD OF MANUFACTURING)
SEMICONDUCTOR DEVICE)

Art Unit: 2812
Examiner: J. Kennedy

CERTIFICATE OF MAILING

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Washington, D.C. 20231, on 4-14-03

Name: Eric Robinson

AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

Sir:

In response to the Official Action dated December 12, 2002, please amend the
above-identified application as follows:

IN THE CLAIMS:

Please amend claims as follows:

1. (Amended) A method of manufacturing a semiconductor device
comprising the steps of:

forming a semiconductor film comprising silicon over an insulating
substrate;

forming a chemical oxide film on a surface of the semiconductor film
comprising silicon as a pretreatment;

doping the semiconductor film comprising silicon with impurity ions after
forming the chemical oxide film; and

forming at least one channel region comprising a portion of the doped
semiconductor film.

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